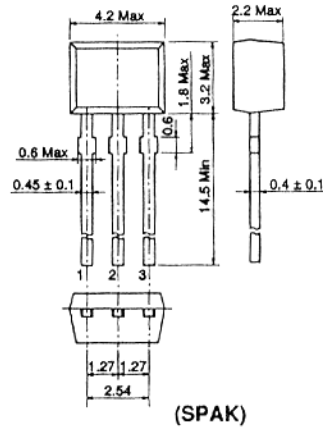


2SA1350

SILICON PNP EPITAXIAL

LOW FREQUENCY LOW NOISE AMPLIFIER
HF AMPLIFIER

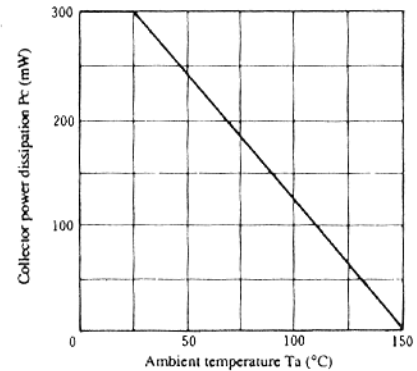


1. Emitter
 2. Collector
 3. Base
- (Dimensions in mm)

■ ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

Item	Symbol	2SA1350	Unit
Collector to base voltage	V _{CB0}	-40	V
Collector to emitter voltage	V _{CE0}	-30	V
Emitter to base voltage	V _{EB0}	-5	V
Collector current	I _C	-100	mA
Collector power dissipation	P _C	300	mW
Junction temperature	T _J	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

MAXIMUM COLLECTOR DISSIPATION CURVE



■ ELECTRICAL CHARACTERISTICS (Ta=25°C)

Item	Symbol	Test Condition	min.	typ.	max.	Unit
Collector to base breakdown voltage	V _{(BR)CBO}	I _C = -10μA, I _E = 0	-40	—	—	V
Collector to emitter breakdown voltage	V _{(BR)CEO}	I _C = -1mA, R _{BE} = ∞	-30	—	—	V
Emitter to base breakdown voltage	V _{(BR)EBO}	I _E = -10μA, I _C = 0	-5	—	—	V
Collector cutoff current	I _{CBO}	V _{CB} = -18V, I _E = 0	—	—	-0.5	μA
Emitter cutoff current	I _{EBO}	V _{EB} = -2V, I _C = 0	—	—	-0.5	μA
DC current transfer ratio	h _{FE} *	V _{CE} = -12V, I _C = -2mA	100	—	500	
Base to emitter voltage	V _{BE}	V _{CE} = -12V, I _C = -2mA	—	—	-0.75	V
Collector to emitter saturation voltage	V _{CE(sat)}	I _C = -10mA, I _B = -1mA	—	—	-0.2	V
Gain bandwidth product	f _r	V _{CE} = -12V, I _C = -2mA	—	200	—	MHz
Collector output capacitance	C _{ob}	V _{CB} = -10V, I _E = 0, f = 1MHz	—	—	4.5	pF
Noise figure	NF	V _{CE} = -6V, I _C = -0.1mA, R _g = 1kΩ, f = 1kHz	—	1.0	5.0	dB

* The 2SA1350 is grouped by h_{FE} as follows.

B	C	D
100 to 200	160 to 320	250 to 500

■ See characteristic curves of 2SA1031.